# TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor SCHS192B

#### January 1998 - Revised May 2003

# CD54HCT640, CD74HCT640

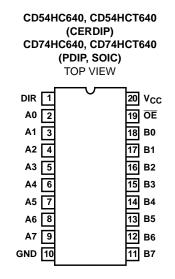
CD54HC640, CD74HC640,

# High-Speed CMOS Logic Octal Three-State Bus Transceiver, Inverting

## Features

- Buffered Inputs
- Three-State Outputs
- Applications in Multiple-Data-Bus Architecture
- Fanout (Over Temperature Range)
  - Standard Outputs..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N<sub>IL</sub> = 30%, N<sub>IH</sub> = 30% of V<sub>CC</sub> at V<sub>CC</sub> = 5V
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility, V<sub>IL</sub>= 0.8V (Max), V<sub>IH</sub> = 2V (Min)
  - CMOS Input Compatibility, IJ  $\leq$  1µA at VOL, VOH

### Pinout



## Description

The 'HC640 and 'HCT640 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads. The 'HC640 and 'HCT640 are inverting buffers.

The direction of data flow (A to B, B to A) is controlled by the DIR input.

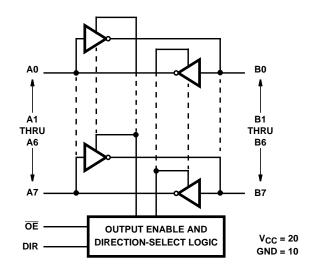
Outputs are enabled by a low on the Output Enable input  $(\overline{OE})$ ; a high  $\overline{OE}$  puts these devices in the high impedance mode.

# **Ordering Information**

PART NUMBER	TEMP. RANGE ( <sup>O</sup> C)	PACKAGE
CD54HC640F3A	-55 to 125	20 Ld CERDIP
CD54HCT640F3A	-55 to 125	20 Ld CERDIP
CD74HC640E	-55 to 125	20 Ld PDIP
CD74HC640M	-55 to 125	20 Ld SOIC
CD74HCT640E	-55 to 125	20 Ld PDIP
CD74HCT640M	-55 to 125	20 Ld SOIC

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures. Copyright © 2003, Texas Instruments Incorporated

# Functional Diagram



#### TRUTH TABLE

CONTRO	L INPUTS	DATA PORT STATUS				
ŌĒ	DIR	A <sub>n</sub>	B <sub>n</sub>			
L	L	ō	I			
н	Н	Z	Z			
н	L	Z	Z			
L	Н	I	ō			

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with  $1k\Omega$  to  $1M\Omega$  resistors.

H = High Level

L = Low Level

I = Input

 $\overline{O}$  = Output (Inversion of Input Level)

Z = High Impedance

## **Absolute Maximum Ratings**

DC Supply Voltage, V <sub>CC</sub> 0.5V to 7V DC Input Diode Current, I <sub>IK</sub>
For $V_{l} < -0.5V$ or $V_{l} > V_{CC} + 0.5V$ ±20mA
DC Output Diode Current, IOK
For $V_0 < -0.5V$ or $V_0 > V_{CC} + 0.5V$
DC Drain Current, per Output, I <sub>O</sub>
For -0.5V < V <sub>O</sub> < V <sub>CC</sub> + 0.5V±35mA
DC Output Source or Sink Current per Output Pin, IO
For $V_0 > -0.5V$ or $V_0 < V_{CC} + 0.5V$ ±25mA
DC V <sub>CC</sub> or Ground Current, I <sub>CC</sub> ±50mA

## **Operating Conditions**

Temperature Range, T <sub>A</sub>
Supply Voltage Range, V <sub>CC</sub>
HC Types
HCT Types4.5V to 5.5V
DC Input or Output Voltage, VI, VO 0V to VCC
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

## **Thermal Information**

Thermal Resistance (Typical, Note 1)	θ <sub>JA</sub> ( <sup>o</sup> C/W)
E (PDIP) Package	. 69
M (SOIC) Package	. 58
Maximum Junction Temperature	150 <sup>0</sup> C
Maximum Storage Temperature Range	-65 <sup>o</sup> C to 150 <sup>o</sup> C
Maximum Lead Temperature (Soldering 10s)	
(SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

# **DC Electrical Specifications**

		TE: CONDI		v <sub>cc</sub>	25 <sup>0</sup> C			-40°C TO 85°C		-55 <sup>°</sup> C TO 125 <sup>°</sup> C		
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(Ÿ)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES		-					_	_		_		
High Level Input	VIH	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	VIL	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output	1		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	μA

# CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

## DC Electrical Specifications (Continued)

		TEST CONDITIONS		v <sub>cc</sub>	25°C			-40°C TO 85°C		-55°C TO 125°C			
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS	
Quiescent Device Current	Icc	V <sub>CC</sub> or GND	0	6	-	-	8	-	80	-	160	μA	
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5	-	±10	μΑ	
HCT TYPES													
High Level Input Voltage	VIH	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V	
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V	
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V	
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V	
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V	
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V	
Input Leakage Current	lı	V <sub>CC</sub> and GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA	
Quiescent Device Current	Icc	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	μA	
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5	-	-	±0.5	-	±5	-	±10	μA	
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI <sub>CC</sub> (Note 2)	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ	

NOTE:

2. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

## **HCT Input Loading Table**

INPUT	UNIT LOADS
DIR	0.9
OE, A	1.5
В	1.5

NOTE: Unit Load is  $\Delta I_{CC}$  limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

# CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

		TEST			25 <sup>0</sup> C			С ТО °С		С ТО 5°С	
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay	t <sub>PHL</sub> , t <sub>PLH</sub>	$C_L = 50 pF$									Γ
A to $\overline{B}$ B to $\overline{A}$			2	-	-	90	-	115	-	135	ns
			4.5	-	-	18	-	23	-	27	ns
		C <sub>L</sub> = 15pF	5	-	7	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	15	-	20	-	23	ns
Output High-Z To High Level,	<sup>t</sup> PHL, <sup>t</sup> PLH	$C_L = 50 pF$	2	-	-	150	-	190	-	225	ns
To Low Level			4.5	-	-	30	-	38	-	45	ns
		C <sub>L</sub> = 15pF	5	-	12	-	-	-	-	-	ns
		$C_L = 50 pF$	6	-	-	26	-	33	-	38	ns
Output High Level	t <sub>PHZ</sub> , t <sub>PLZ</sub>	C <sub>L</sub> = 50pF	2	-	-	150	-	190	-	225	ns
Output Low Level to High Z			4.5	-	-	30	-	38	-	45	ns
		C <sub>L</sub> = 15pF	5	-	12	-	-	-	-	-	ns
		C <sub>L</sub> = 50pF	6	-	-	26	-	33	-	38	ns
Output Transition Time	t <sub>THL</sub> , t <sub>TLH</sub>	C <sub>L</sub> = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C <sub>IN</sub>	C <sub>L</sub> = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C <sub>PD</sub>	-	5	-	38	-	-	-	-	-	pF
HCT TYPES			<u>.</u>								<u>.</u>
Propagation Delay											
A to $\overline{B}$ B to $\overline{A}$	<sup>t</sup> PHL, <sup>t</sup> PLH	$C_L = 50 pF$	4.5	-	-	22	-	28	-	33	ns
D IO A		C <sub>L</sub> = 15pF	5	-	9	-	-	-	-	-	ns
Output High-Z	t <sub>PHL,</sub> t <sub>PLH</sub>	$C_L = 50 pF$	4.5	-	-	30	-	38	-	45	ns
To High Level, To Low Level		C <sub>L</sub> = 15pF	5	-	12	-	-	-	-	-	ns
Output High Level	t <sub>PHZ</sub> , t <sub>PLZ</sub>	C <sub>L</sub> = 50pF	4.5	-	-	30	-	38	-	45	ns
Output Low Level to High Z		C <sub>L</sub> = 15pF	5	-	12	- 1	-	-	-	-	ns
Output Transition Time	t <sub>THL</sub> , t <sub>TLH</sub>	$C_L = 50 pF$	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C <sub>IN</sub>	C <sub>L</sub> = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	CO	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C <sub>PD</sub>	-	5	-	41	-	-	-	-	-	pF

NOTES:

3.  $C_{PD}$  is used to determine the dynamic power consumption, per channel. 4.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

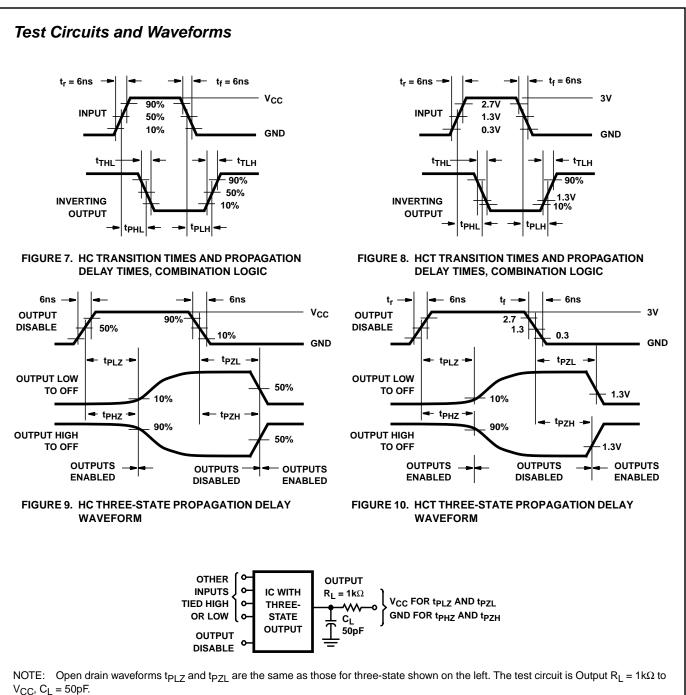


FIGURE 11. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT



25-Sep-2013

# **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	-	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)		(3)		(4/5)	
5962-8974001RA	ACTIVE	CDIP	J	20	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-8974001RA CD54HCT640F3A	Samples
CD54HC640F3A	ACTIVE	CDIP	J	20	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-8780901RA CD54HC640F3A	Samples
CD54HCT640F3A	ACTIVE	CDIP	J	20	1	TBD	A42	N / A for Pkg Type	-55 to 125	5962-8974001RA CD54HCT640F3A	Samples
CD74HC640E	ACTIVE	PDIP	Ν	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC640E	Samples
CD74HC640EE4	ACTIVE	PDIP	Ν	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC640E	Samples
CD74HC640M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC640M	Samples
CD74HC640ME4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC640M	Samples
CD74HC640MG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC640M	Samples
CD74HCT640E	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT640E	Samples
CD74HCT640EE4	ACTIVE	PDIP	Ν	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT640E	Samples
CD74HCT640M	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT640M	Samples
CD74HCT640ME4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT640M	Samples
CD74HCT640MG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT640M	Samples

<sup>(1)</sup> The marketing status values are defined as follows: **ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.



25-Sep-2013

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(<sup>5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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#### OTHER QUALIFIED VERSIONS OF CD54HC640, CD54HCT640, CD74HC640, CD74HCT640 :

• Catalog: CD74HC640, CD74HCT640

• Military: CD54HC640, CD54HCT640

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

J (R-GDIP-T\*\*) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

# N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AC.



# LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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Products		Applications	
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Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
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